

Silicon PNP Power Transistors

2SB555 2SB556

DESCRIPTION

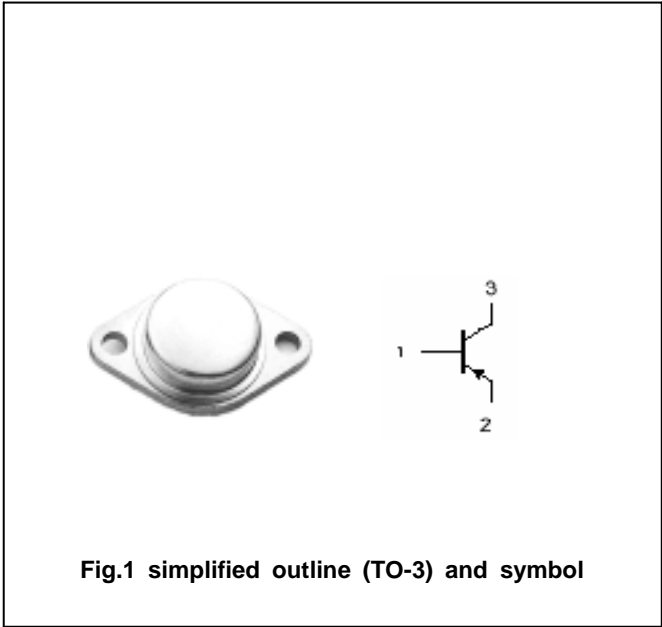
- With TO-3 package
- Complement to type 2SD425/426
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	Open emitter	2SB555	-140	V
			2SB556	-120	
V _{CEO}	Collector-emitter voltage	Open base	2SB555	-140	V
			2SB556	-120	
V _{EBO}	Emitter-base voltage	Open collector	-5	V	
I _C	Collector current		-12	A	
I _E	Emitter current		12	A	
P _C	Collector power dissipation	T _C =25	100	W	
T _j	Junction temperature		150		
T _{stg}	Storage temperature		-65~150		

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB555	I _C =-0.1A ; I _B =0	-140		V
		2SB556		-120		
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	2SB555			-3.0	V
		2SB556				
V _{BE}	Base-emitter on voltage	I _C =-7A ; V _{CE} =-5V			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-2A ; V _{CE} =-5V	40		140	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-10V; f=1.0MHz		330		pF
f _T	Transition frequency	I _C =-2A ; V _{CE} =-5V		6		MHz

PACKAGE OUTLINE

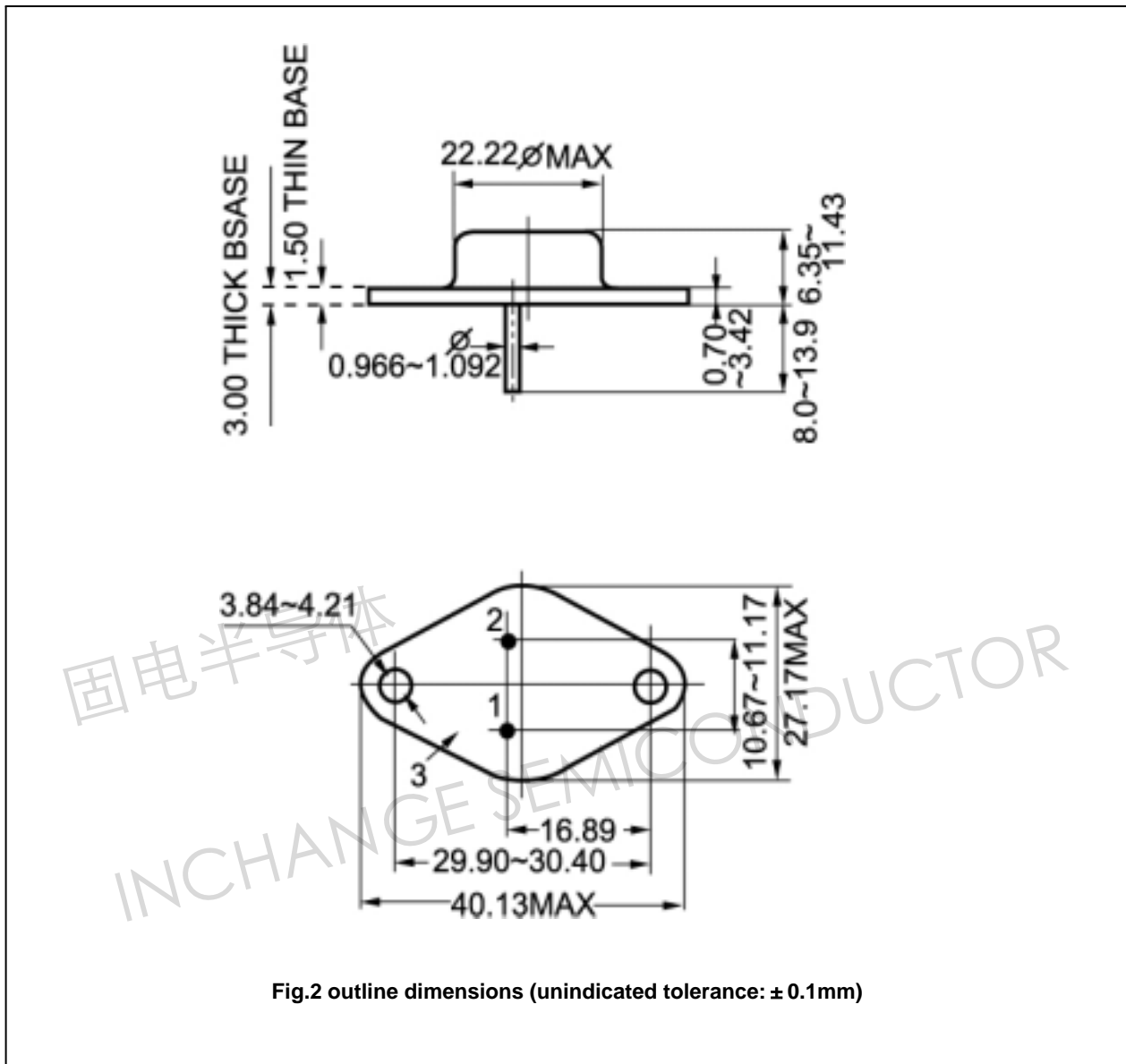


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)